Data Sheet

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Manufacturers of World Class Discrete Semiconductors

MPQ2907A

PNP SILICON QUAD TRANSISTOR

JEDEC TO-116 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR MPQ2907A type is comprised of four independent Silicon PNP Transistors mounted in a 14 PIN DIP, designed for general purpose amplfier and switching applications.

MAXIMUM RATINGS (T_A=25°C)

	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	60	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Collector Current	I_C	600	mA
Power Dissipation (Each Transistor)	P_D	650	mW
Power Dissipation (Total Package)	P_D	1.9	W
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	°C

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{CBO}	V_{CB}=30V			50	nA
I_{EBO}	V_{CE}=3.0V			50	nA
BV_{CEO}	I_C=10mA	60			V
BV_{CBO}	I_C=10uA,	60			V
BV_{EBO}	I_E=10uA	5.0			V
$V_{CE(SAT)}$	I_C=150mA, I_B=15mA			0.4	V
$V_{CE(SAT)}$	I_C=300mA, I_B=30mA			1.6	V
$V_{BE(SAT)}$	I_C=150mA, I_B=15mA			1.3	V
$V_{BE(SAT)}$	I_C=300mA, I_B=30mA			2.6	V
h_{FE}	V_{CE}=10V, I_C=10mA	75			
h_{FE}	V_{CE}=10V, I_C=150mA	100			
h_{FE}	V_{CE}=10V, I_C=300mA	50			
f_T	V_{CE}=20V, I_C=50mA, f=100MHz	200			MHz
C_{ib}	V_{BE}=2.0V, I_C=0, f=1.0kHz		6.0	8.0	pF
C_{ob}	V_{CB}=10V, I_E=0, f=1.0kHz		20	30	pF
t_{on}	V_{CC}=30V, I_C=150mA, I_{B1}=15mA		30		ns
t_{off}	V_{CC}=30V, I_C=150mA, I_{B1}=I_{B2}=15mA		150		ns